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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants:

Sang Young KIM, et al.

Examiner: A. Everhart

Serial No.:

07/964,362

Group Art Unit: 1104

Filed:

10/21/92

Docket: 99

9983.3US01

Title:

METHOD FOR FILLING CONTACT HOLES WITH METAL BY

TWO-STEP DEPOSITION

AMENDMENT

Hon. Commissioner of Patents and Trademarks Washington, D.C. 20231

Sir:

In response to the Office Action mailed October 21,
1993, regarding the above-identified patent application,
Applicants respectfully request the following amendments be made.

IN THE CLAIMS

Amend the claims as follows:

2. (Once Amended) The methods of claim 1, wherein the [first contact hole and the second contact hole are filled with the] first metal layer and subsequently the second metal layer [of selective tungsten layer, respectively,] are formed by chemical vapor deposition method.

Add the following new claims: